

Amendments to the Specification:

On page 1, on the first line below the title, replace the subheading “Technical Field” with the subheading --BACKGROUND OF THE INVENTION--.

On page 1, after the first paragraph, delete the subheading “Background Art”.

On page 2, line 13, replace the subheading “Disclosure of the Invention” with the subheading --SUMMARY OF THE INVENTION--.

On page 3, line 20, delete the subheading “Effect of the Invention”.

On page 4, line 5, replace the subheading “Best Mode for Carrying Out the Invention” with the subheading --DETAILED DESCRIPTION OF THE INVENTION--.

On page 7, in the first row of TABLE 1, replace the column heading “Example 2” with the column heading --Reference Example--.

On page 7, in the first row of TABLE 1, replace the column heading “Example 3” with the column heading --Example 2--.

On page 10, line 1, replace the subheading “(Example 2)” with the subheading --(Reference Example)--.

Amend the paragraph on page 10, lines 6-11, as follows:

As shown in Table 1, although slightly inferior to Example 1, only Fe was 7.6wtppm, and the other impurities have been reduced to 1wtppm or 0.1wtppm or less, and high purity copper sulfate having a purity level of 4N to 5N ~~or higher~~ was obtained. Further, when this high purity copper sulfate was redissolved ~~and was filtered~~, there was no undissolved residue ~~of in water when filtered at 1 μ m or greater in water more~~.

Amend the paragraph on page 10, lines 12-16, as follows:

With the processes shown in the Reference Example, 2 ~~of the present invention, a significant~~ although an improvement in purity is less than Example 1, a reasonable improvement in purity has been confirmed. These impurities are particularly disfavored in the copper plating to circuits or wirings upon manufacturing a semiconductor device or the like, and the reduction of such impurities is extremely effective.

On page 10, line 17, replace the subheading “(Example 3)” with the subheading --(Example 2)--.

Amend the paragraph on page 10, lines 21-25, as follows:

As shown in Table 1, impurities have been reduced to 1wtppm or 0.1wtppm or less, and high purity copper sulfate having a purity level of 4N to 5N ~~or higher~~ was obtained. Further, when this high purity copper sulfate was redissolved ~~and was filtered~~, there was no undissolved residue ~~of in water when filtered at 1 μ m or greater in water when more~~.

Amend the paragraph on page 10, line 26, to page 11, line 2, as follows:

With the processes shown in Example 3 2 of the present invention, a significant improvement in purity has been confirmed. These impurities are particularly disfavored in the copper plating to circuits or wirings upon manufacturing a semiconductor device or the like, and the reduction of such impurities is extremely effective.

On page 11, line 17, delete the subheading “Industrial Applicability”.